BLF6G27-100; BLF6G27LS-100

WiMAX power LDMOS transistor Rev. 02 — 8 July 2010

Product data sheet

Product profile 1.

1.1 General description

100 W LDMOS power transistor for base station applications at frequencies from 2500 MHz to 2700 MHz.

Table 1. **Typical performance**

Typical RF performance at T_{case} = 25 °C in a class-AB production test circuit.

Mode of operation	f	V_{DS}	P _{L(AV)}	Gp	ηD	ACPR _{885k}	ACPR _{1980k}	ACPR _{5M}	ACPR _{10M}
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)	(dBc)	(dBc)	(dBc)
BLF6G27-100									
1-carrier W-CDMA [1]	2500 to 2700	28	14	16.5	23	-	-	-40	-59
1-carrier N-CDMA [2]	2500 to 2700	28	14	17	23	-50 <u>[3]</u>	-65 <u>[3]</u>	-	-
BLF6G27LS-100									
1-carrier W-CDMA [1]	2500 to 2700	28	14	17	23	-	-	-41	-60
1-carrier N-CDMA [2]	2500 to 2700	28	14	17	23	-50 <u>[3]</u>	-65 <u>[3]</u>	-	-

^[1] Signal is a one carrier, TM1 W-CDMA signal with 64 DPCH and 100 % clipping. PAR is 9.65 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Typical 1-carrier W-CDMA performance (single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability on the CCDF; channel bandwidth is 3.84 MHz) at a frequency of 2500 MHz, 2600 MHz and 2700 MHz, a supply voltage of 28 V and an I_{Dq} of 900 mA:
 - Average output power = 14 W
 - ◆ Power gain = 17 dB
 - Drain efficiency = 23 %
 - ◆ ACPR_{5M} = -41 dBc
- Typical 1-carrier N-CDMA performance (single carrier IS-95 with pilot, paging, sync and 6 traffic channels [Walsh codes 8 to 13]. PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz) at a frequency of 2500 MHz, 2600 MHz and 2700 MHz, a supply voltage of 28 V and an I_{Dq} of 900 mA:
 - Average output power = 14 W
 - Power gain = 17 dB
 - Drain efficiency = 23 %
 - ◆ ACPR_{885k} = -50 dBc (within 30 kHz bandwidth)



Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

Measured within 30 kHz bandwidth.

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (2500 MHz to 2700 MHz)
- Internally matched for ease of use

1.3 Applications

 RF power amplifiers for base stations and multicarrier applications in the 2500 MHz to 2700 MHz frequency range

2. Pinning information

Table 2. Pinning

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
BLF6G27	′-100 (SOT502A)		
1	drain		
2	gate	$\begin{array}{c c} & & \\ & & \\ & & \\ \end{array}$	ئے
3	source	[1]	2
			· 3 sym112
			Syminz
BLF6G27	'LS-100 (SOT502B)		
1	drain		
2	gate	3	1
3	source	[1]	2
			3
			sym112

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BLF6G27-100	-	flanged LDMOST ceramic package; 2 mounting holes; 2 leads	SOT502A			
BLF6G27LS-100	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Min	Max	Unit
V_{DS}	drain-source voltage	-	65	V
V_{GS}	gate-source voltage	-0.5	+13	V
I_D	drain current	-	29	А
T _{stg}	storage temperature	-65	+150	°C
T _i	junction temperature	-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Туре	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from	T_{case} = 80 °C; P_L = 100 W	BLF6G27-100	0.68	K/W
	junction to case		BLF6G27LS-100	0.5	K/W

6. Characteristics

Table 6. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.5 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 150 \text{ mA}$	1.4	2	2.4	V
I_{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	5	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	22.3	27	-	Α
I_{GSS}	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	450	nA
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 5.25 \text{ A}$	-	10.5	-	S
$R_{DS(on)} \\$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.25 \text{ A}$	-	0.1	0.16	Ω
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V};$ f = 1 MHz	-	2.4	-	pF

7. Application information

Table 7. Application information

Mode of operation: 1-carrier W-CDMA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability on the CCDF; carrier channel bandwidth is 3.84 MHz; f_1 = 2500 MHz; f_2 = 2600 MHz, f_3 = 2700 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 900 mA; T_{case} = 25 °C; unless otherwise specified, in a class-AB production circuit.

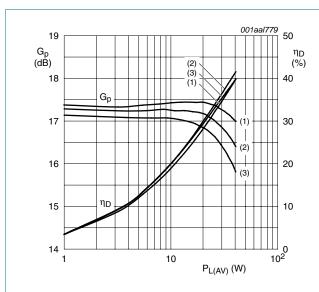
		•					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
G_p	power gain	$P_{L(AV)} = 14 W$					
		BLF6G27-100		14.8	16.5	-	dB
		BLF6G27LS-100		15	17	-	dB
RLin	input return loss	$P_{L(AV)} = 14 W$		-	-10	-6	dB
η _D	drain efficiency	$P_{L(AV)} = 14 W$		20	23	-	%
ACPR _{5M}	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 14 W$	[1]				
		BLF6G27-100		-	-40	-36	dBc
		BLF6G27LS-100		-	-41	-37	dBc
ACPR _{10M}	adjacent channel power ratio (10 MHz)	$P_{L(AV)} = 14 W$	[1]				
		BLF6G27-100		-	-59	-56	dBc
		BLF6G27LS-100		-	-60	-57	dBc

^[1] ACPR measured in 3.84 MHz channel bandwidth at ± 5 MHz and ± 10 MHz.

7.1 Ruggedness in class-AB operation

The BLF6G27-100 and BLF6G27LS-100 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 900 \text{ mA}$; $P_L = 100 \text{ W}$ (CW); f = 2500 MHz.

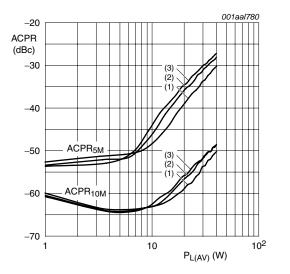
7.2 Single carrier W-CDMA performance



 $V_{DS}=28$ V; $I_{Dq}=900$ mA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability; channel bandwidth = 3.84 MHz.

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 1. Power gain and drain efficiency as a function of average output power; typical values

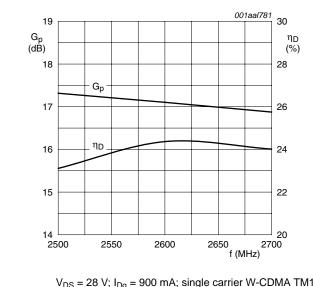


 V_{DS} = 28 V; I_{Dq} = 900 mA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability; channel bandwidth = 3.84 MHz.

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

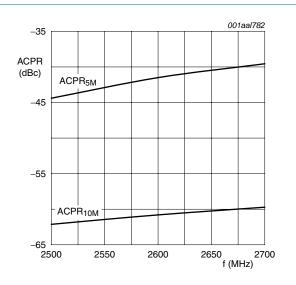
Fig 2. ACPR at 5 MHz and at 10 MHz as a function of average output power; typical values

7.3 Single carrier W-CDMA broadband performance at 14 W average power



 $V_{DS} = 28 \text{ V}$; $I_{Dq} = 900 \text{ mA}$; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability; channel bandwidth = 3.84 MHz.

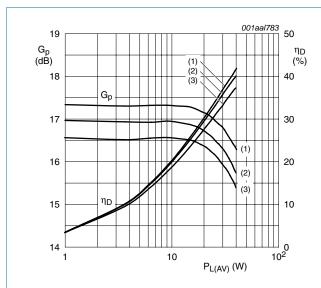
Power gain and drain efficiency as a function Fig 3. of frequency; typical values



 V_{DS} = 28 V; I_{Dq} = 900 mA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability; channel bandwidth = 3.84 MHz.

Fig 4. ACPR at 5 MHz and at 10 MHz as a function of frequency; typical values

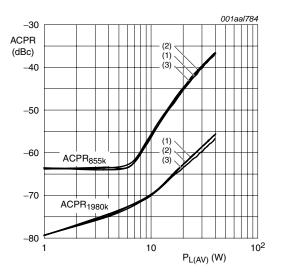
7.4 IS-95 performance



 $V_{DS}=28\ V;\ I_{Dq}=900\ mA;\ IS-95\ with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth = 1.2288 MHz.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 5. Power gain and drain efficiency as a function of average output power; typical values

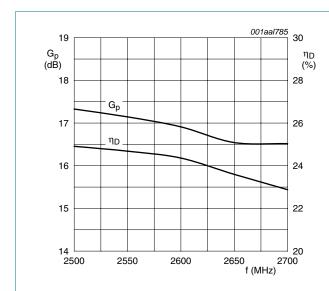


 $V_{DS}=28\ V;\ I_{Dq}=900\ mA;\ IS-95$ with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth = 1.2288 MHz.

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

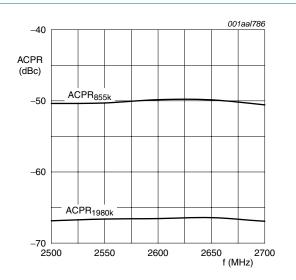
Fig 6. ACPR at 885 kHz and at 1980 kHz as a function of average output power; typical values

7.5 IS-95 broadband performance at 14 W average power



 $V_{DS}=28\ V;\ I_{Dq}=900\ mA;\ IS-95$ with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth = 1.2288 MHz.

Fig 7. Power gain and drain efficiency as a function of frequency; typical values



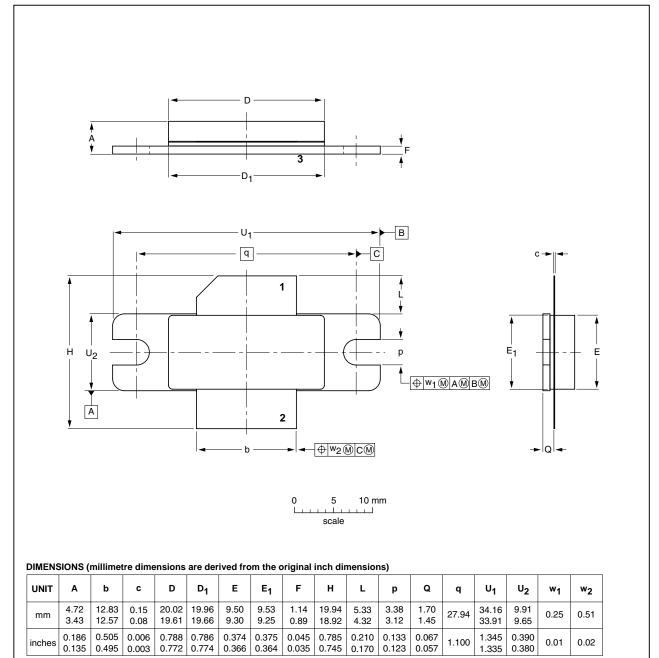
 V_{DS} = 28 V; I_{Dq} = 900 mA; IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth = 1.2288 MHz.

Fig 8. ACPR at 885 kHz and at 1980 kHz as a function of frequency; typical values

8. Package outline



SOT502A



OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT502A					99-12-28 03-01-10

Fig 9. Package outline SOT502A

BLF6G27-100_BLF6G27LS-100

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Earless flanged LDMOST ceramic package; 2 leads

SOT502B

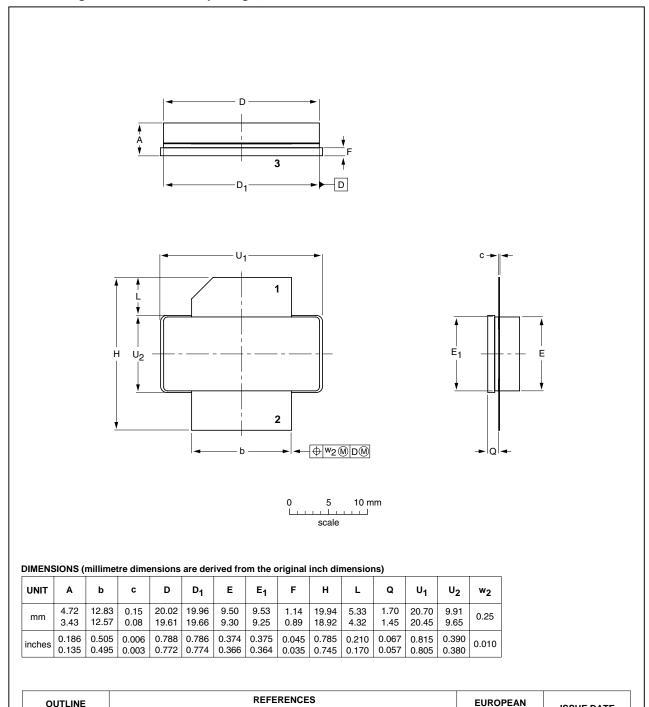


Fig 10. Package outline SOT502B

IEC

JEDEC

VERSION

SOT502B

JEITA

ISSUE DATE

03-01-10

PROJECTION

9. Abbreviations

Table 8. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
FCH	Frame Control Header
FFT	Fast Fourier Transform
IBW	Instantaneous BandWidth
IS-95	Interim Standard 95
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
N-CDMA	Narrowband Code Division Multiple Access
PAR	Peak-to-Average power Ratio
PUSC	Partial Usage of SubChannels
RF	Radio Frequency
TM1	Test Model 1
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access
WCS	Wireless Communications Service
WiMAX	Worldwide interoperability for Microwave Access

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF6G27-100_BLF6G27LS-100 v.2	20100708	Product data sheet	-	BLF6G27-100_ BLF6G27LS-100_1
Modifications:	 Data sheet 	status change to Product	data sheet.	
	• Table 1 on BLF6G27L	page 1: A distinction has l S-100	peen made betwee	n BLF6G27-100 and
	• Table 7 on BLF6G27L	page 4: A distinction has l S-100	peen made betwee	n BLF6G27-100 and
BLF6G27-100_BLF6G27LS-100_1	20100503	Preliminary data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BLF6G27-100_BLF6G27LS-100

BLF6G27-100; BLF6G27LS-100

WiMAX power LDMOS transistor

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